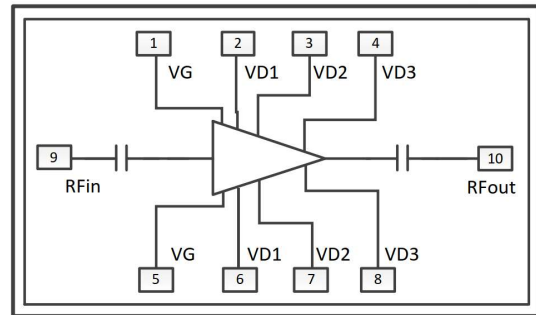


### Performance

- Frequency: 6-18GHz
- Pout: 43dBm @28V
- PAE: 22%
- Large Signal Gain: 15dB
- Small Signal Gain: 25dB
- Bias:  $V_d=28V$ ,  $I_{dq}=2.5A$
- Size: 4.5\*5.2mm\*0.08mm
- Performance under CW operation

### Function Diagram

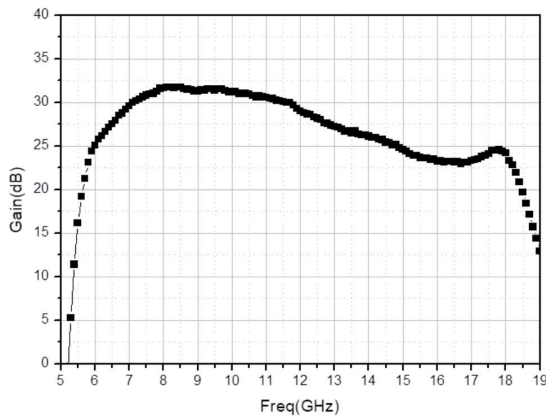


### Electrical Specifications ( $V_d=28V$ , $I_{dq}=2.5A$ , $V_g=-1.8V$ , F: 6-18GHz, CW)

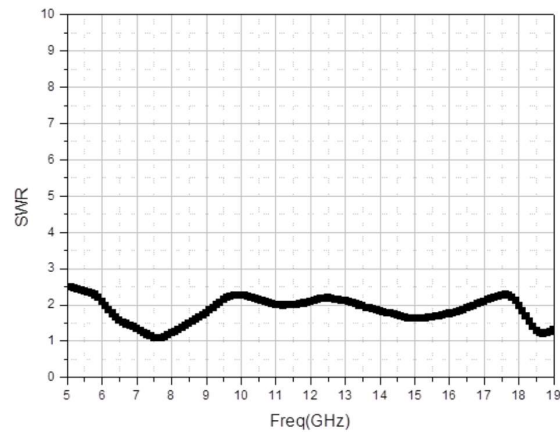
Parameter	Min	Typical	Max	Unit
Small Signal Gain @ $P_{IN}=-15dBm$	-	25	-	dB
Large Signal Gain @ $P_{IN}=26dBm$	-	15	-	dB
Saturated Power @ $P_{IN}=26dBm$	-	43	-	dBm
Power Added Efficiency @ $P_{IN}=26dBm$	-	22	-	%

### Test Curves ( $V_d=28V$ , $V_g=-1.8V$ , F: 6-18GHz, CW)

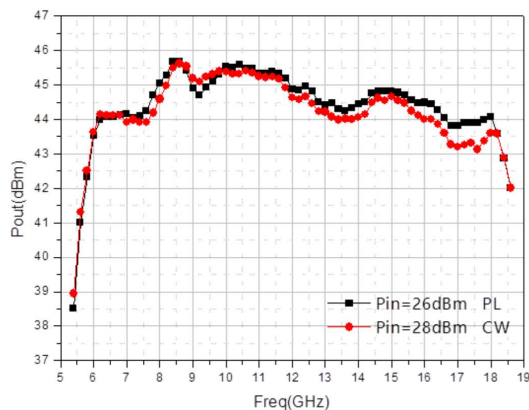
Small Signal Gain vs. Freq ( $P_{IN}=-15dBm$ )



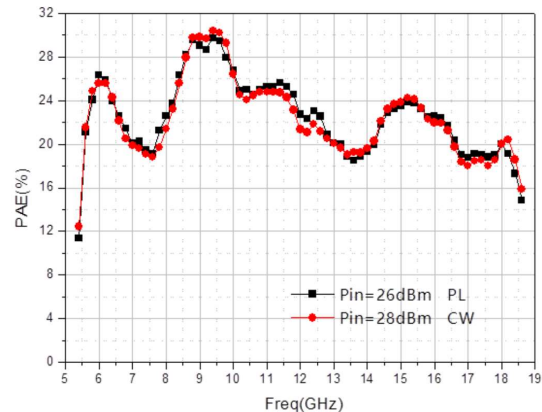
Input VSWR vs. Freq ( $P_{IN}=-15dBm$ )



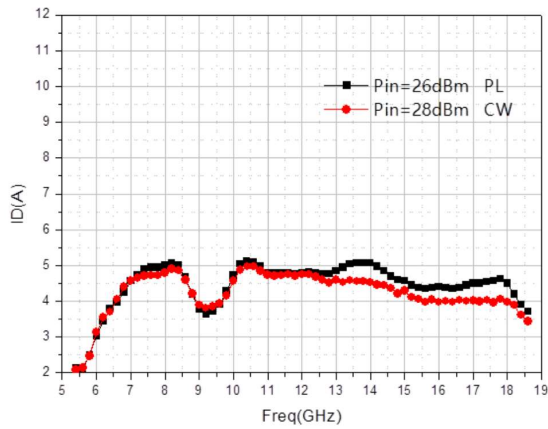
Saturated Power vs. Freq ( $P_{IN}=26dBm$ )



PAE vs. Freq ( $P_{IN}=26dBm$ )



Drain Current vs. Freq (P<sub>IN</sub>=26dBm)

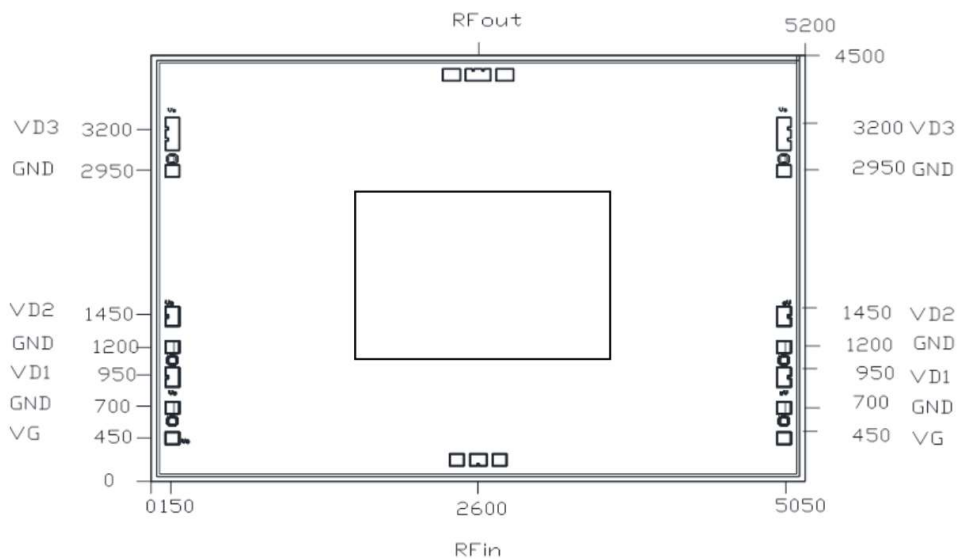


**Absolute Max Ratings (T<sub>A</sub>=25°C)**

Symbol	Parameter	Value	Remark
V <sub>d</sub>	Drain Voltage	32 V	
I <sub>d</sub>	Drain Current	6.0 A	
V <sub>g</sub>	Gate Voltage	-10 V	
I <sub>g</sub>	Gate Current	50 mA	
P <sub>d</sub>	DC Power	120 W	
P <sub>in</sub>	Input Power	32 dBm	
T <sub>ch</sub>	Channel Temperature	225°C	
T <sub>m</sub>	Mounting Temperature	310°C	1min, N <sub>2</sub> Protection
T <sub>stg</sub>	Storage Temperature	-55~175°C	

Exceeding any one or combination of these limits may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

**Outline Drawing**



Application Circuit

